<u>Supplementary information:</u> Role of ions in film conformality and quality during plasma-assisted ALD of SiO_2 and TiO_2

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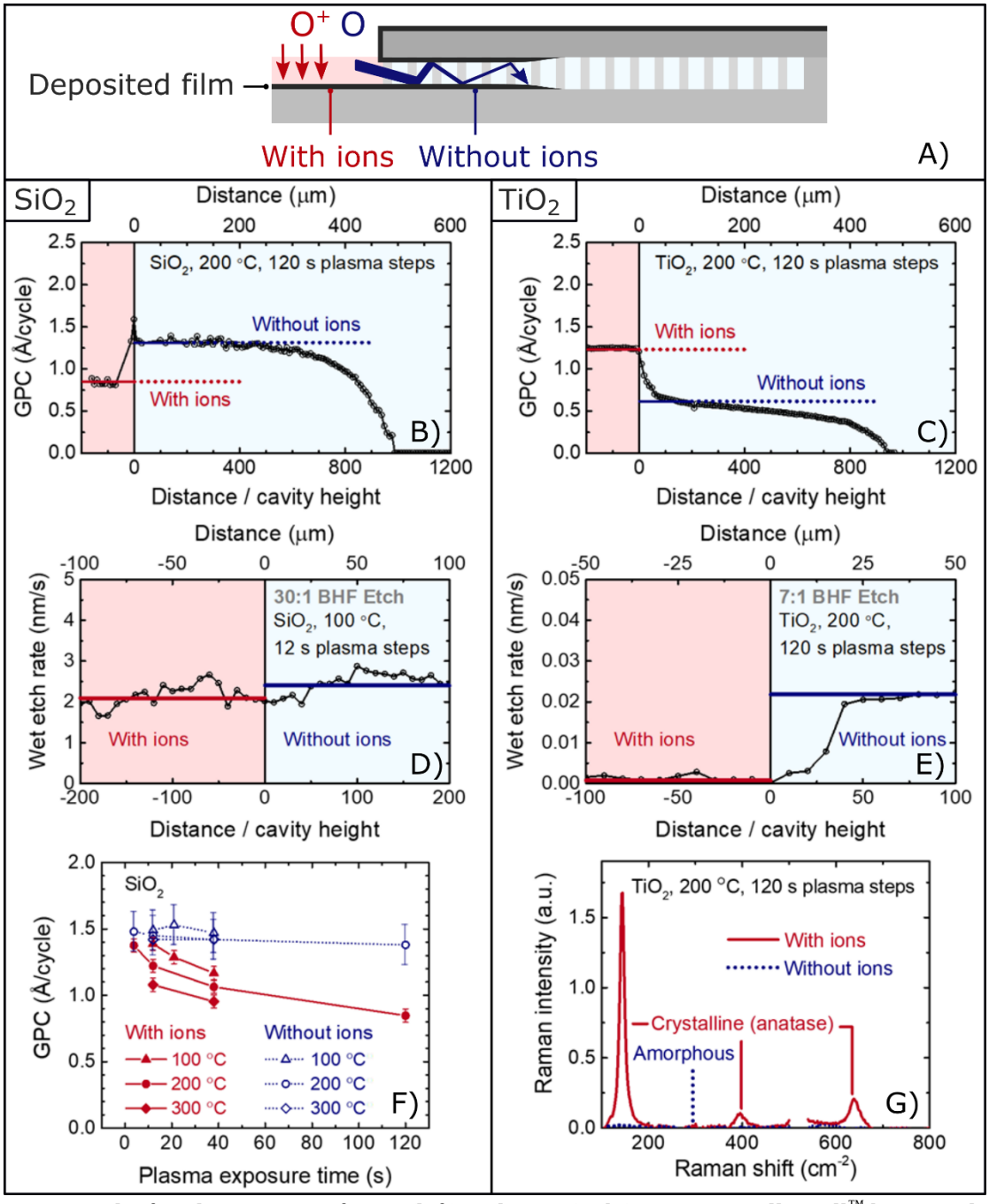

Figure S1: Results for plasma ALD of SiO_2 (left) and TiO_2 (right) grown on PillarHall™ horizontal trench structures (A), revealing differences in growth behavior for the regions with and without exposure to ions. For SiO_2, the growth per cycle (GPC) decreases with exposure to ions (B), but only for extended plasma steps (F). Moreover, the material quality remains similar, as suggested by a relatively uniform wet etch rate (D). For TiO_2, exposure to ions yields crystalline growth rather than amorphous growth (G), with a higher GPC (C) and a strongly reduced wet etch rate (E).